Joan M Redwing

List of Publications by Citations

278 papers	10,164 citations	56 h-index	90 g-index
306 ext. papers	11,331 ext. citations	5.2 avg, IF	6.01 L-index

#	Paper	IF	Citations
278	Two-dimensional gallium nitride realized via graphene encapsulation. *Nature Materials*, **2016**, 15, 1166-1171	27	447
277	In situ epitaxial MgB2 thin films for superconducting electronics. *Nature Materials*, **2002**, 1, 35-8	27	355
276	Highly scalable, atomically thin WSe2 grown via metal-organic chemical vapor deposition. *ACS Nano* , **2015**, 9, 2080-7	16.7	273
275	Bottom-up assembly of large-area nanowire resonator arrays. *Nature Nanotechnology*, **2008**, 3, 88-92	28.7	257
274	High-field superconductivity in alloyed MgB2 thin films. *Physical Review B*, **2005**, 71,	3.3	213
273	Silicon nanowire array photelectrochemical cells. *Journal of the American Chemical Society*, **2007**, 129, 12344-5	16.4	204
272	Crystallographic wet chemical etching of GaN. *Applied Physics Letters*, **1998**, 73, 2654-2656	3.4	194
271	Optical properties of Si-doped GaN. *Applied Physics Letters*, **1997**, 71, 921-923	3.4	190
270	Optical Properties of Rectangular Cross-sectional ZnS Nanowires. *Nano Letters*, **2004**, 4, 1663-1668	11.5	185
269	The role of the tunneling component in the current voltage characteristics of metal-GaN Schottky diodes. *Journal of Applied Physics*, **1998**, 84, 2099-2104	2.5	160
268	An optically pumped GaN AlGaN vertical cavity surface emitting laser. *Applied Physics Letters*, **1996**, 69, 1-3	3.4	154
267	Growth characteristics of silicon nanowires synthesized by vapor liquid solid growth in nanoporous alumina templates. *Journal of Crystal Growth*, **2003**, 254, 14-22	1.6	152
266	Nanometer-scale modification and welding of silicon and metallic nanowires with a high-intensity electron beam. *Small*, **2005**, 1, 1221-9	11	146
265	High voltage (450 V) GaN Schottky rectifiers. *Applied Physics Letters*, **1999**, 74, 1266-1268	3.4	139
264	Diffusion-Controlled Epitaxy of Large Area Coalesced WSe Monolayers on Sapphire. *Nano Letters*, **2018**, 18, 1049-1056	11.5	136
263	Diameter dependent growth rate and interfacial abruptness in vapor-liquid-solid Si/Si1-xGex heterostructure nanowires. *Nano Letters*, **2008**, 8, 1246-52	11.5	134
262	A roadmap for electronic grade 2D materials. *2D Materials*, **2019**, 6, 022001	5.9	133

261	Realizing Large-Scale, Electronic-Grade Two-Dimensional Semiconductors. *ACS Nano*, **2018**, 12, 965-975	16.7	127
260	Use of phosphine as an n-type dopant source for vapor-liquid-solid growth of silicon nanowires. *Nano Letters*, **2005**, 5, 2139-43	11.5	124
259	Superconducting MgB2 thin films on silicon carbide substrates by hybrid physicalchemical vapor deposition. *Applied Physics Letters*, **2003**, 82, 2097-2099	3.4	124
258	Enhancement of the superconducting transition temperature of MgB2 by a strain-induced bond-stretching mode softening. *Physical Review Letters*, **2004**, 93, 147006	7.4	121
257	Schottky barrier engineering in IIIV nitrides via the piezoelectric effect. *Applied Physics Letters*, **1998**, 73, 1880-1882	3.4	120
256	Measuring the specific contact resistance of contacts to semiconductor nanowires. *Solid-State Electronics*, **2005**, 49, 227-232	1.7	117
255	Structural and electrical properties of trimethylboron-doped silicon nanowires. *Applied Physics Letters*, **2004**, 85, 3101-3103	3.4	116
254	Enhanced conversion efficiencies for pillar array solar cells fabricated from crystalline silicon with short minority carrier diffusion lengths. *Applied Physics Letters*, **2010**, 96, 213503	3.4	104
253	Electrochemical Investigation of the Gallium Nitride-Aqueous Electrolyte Interface. *Journal of the Electrochemical Society*, **1995**, 142, L238-L240	3.9	101
252	VaporLiquidSolid Growth of SiliconGermanium Nanowires. *Advanced Materials*, **2003**, 15, 2073-2076	24	100
251	MgB2 thin films by hybrid physicalchemical vapor deposition. *Physica C: Superconductivity and Its Applications*, **2007**, 456, 22-37	1.3	98
250	CapacitanceVoltage characterization of AlN/GaN metalInsulatorSemiconductor structures grown on sapphire substrate by metalorganic chemical vapor deposition. *Journal of Applied Physics*, **2000**, 88, 1983-1986	2.5	97
249	Thickness dependence of the properties of epitaxial MgB2 thin films grown by hybrid physical-chemical vapor deposition. *Applied Physics Letters*, **2003**, 82, 4319-4321	3.4	92
248	Properties of MgB2 thin films with carbon doping. *Applied Physics Letters*, **2004**, 85, 2017-2019	3.4	86
247	Lateral AlxGa1N power rectifiers with 9.7 kV reverse breakdown voltage. *Applied Physics Letters*, **2001**, 78, 823-825	3.4	85
246	Properties of Si donors and persistent photoconductivity in AlGaN. *Solid-State Electronics*, **1998**, 42, 627-635	1.7	82
245	Effect of diborane on the microstructure of boron-doped silicon nanowires. *Journal of Crystal Growth*, **2005**, 277, 428-436	1.6	82
244	Radial junction silicon wire array solar cells fabricated by gold-catalyzed vapor-liquid-solid growth. *Applied Physics Letters*, **2010**, 97, 143108	3.4	81

243	Stranski-Krastanow growth of germanium on silicon nanowires. *Nano Letters*, **2005**, 5, 1081-5	11.5	80
242	Evidence of compensating centers as origin of yellow luminescence in GaN. *Applied Physics Letters*, **1997**, 71, 3224-3226	3.4	79
241	Growth stresses and cracking in GaN films on (111) Si grown by metal-organic chemical-vapor deposition. I. AlN buffer layers. *Journal of Applied Physics*, **2005**, 98, 023514	2.5	79
240	Ni and Ti Schottky barriers on n-AlGaN grown on SiC substrates. *Applied Physics Letters*, **1998**, 73, 238-240	3.4	79
239	Diameter-Controlled Synthesis of Silicon Nanowires Using Nanoporous Alumina Membranes. *Advanced Materials*, **2005**, 17, 114-117	24	74
238	The impact of graphene properties on GaN and AlN nucleation. *Surface Science*, **2015**, 634, 81-88	1.8	73
237	Thermally stable PtSi Schottky contact on n-GaN. *Applied Physics Letters*, **1997**, 70, 1275-1277	3.4	72
236	X-ray photoemission spectroscopic investigation of surface treatments, metal deposition, and electron accumulation on InN. *Applied Physics Letters*, **2003**, 82, 3254-3256	3.4	72
235	Intrinsic stresses in AlN layers grown by metal organic chemical vapor deposition on (0001) sapphire and (111) Si substrates. *Journal of Applied Physics*, **2004**, 96, 2995-3003	2.5	71
234	Lateral Versus Vertical Growth of Two-Dimensional Layered Transition-Metal Dichalcogenides: Thermodynamic Insight into MoS2. *Nano Letters*, **2016**, 16, 5742-50	11.5	70
233	Critical current density and resistivity of MgB2 films. *Applied Physics Letters*, **2003**, 83, 102-104	3.4	70
232	Defect-Controlled Nucleation and Orientation of WSe on hBN: A Route to Single-Crystal Epitaxial Monolayers. *ACS Nano*, **2019**, 13, 3341-3352	16.7	70
231	Persistent photoconductivity and defect levels in n-type AlGaN/GaN heterostructures. *Applied Physics Letters*, **1998**, 72, 2745-2747	3.4	69
230	Fabrication and characterization of axially doped silicon nanowire tunnel field-effect transistors. *Nano Letters*, **2010**, 10, 4813-8	11.5	67
229	Benchmarking monolayer MoS and WS field-effect transistors. *Nature Communications*, **2021**, 12, 693	17.4	66
228	Template-directed vapor□liquid□solid growth of silicon nanowires. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2002**, 20, 389		64
227	Fabrication and electrical properties of si nanowires synthesized by Al catalyzed vapor-liquid-solid growth. *Nano Letters*, **2009**, 9, 4494-9	11.5	63
226	Interfacial reactions between nickel thin films and GaN. *Journal of Applied Physics*, **1997**, 82, 650-654	2.5	63

225	Lateral variations in threshold voltage of an AlxGa1□N/GaN heterostructure field-effect transistor measured by scanning capacitance spectroscopy. *Applied Physics Letters*, **2001**, 78, 88-90	3.4	57
224	An Al/sub 0.3/Ga/sub 0.7/N/GaN undoped channel heterostructure field effect transistor with Fmax of 107 GHz. *IEEE Electron Device Letters*, **1999**, 20, 323-325	4.4	57
223	A low-power biomimetic collision detector based on an in-memory molybdenum disulfide photodetector. *Nature Electronics*, **2020**, 3, 646-655	28.4	57
222	Large anisotropic normal-state magnetoresistance in clean MgB2 thin films. *Physical Review Letters*, **2006**, 96, 167003	7.4	55
221	Growth stresses and cracking in GaN films on (111) Si grown by metalorganic chemical vapor deposition. II. Graded AlGaN buffer layers. *Journal of Applied Physics*, **2005**, 98, 023515	2.5	52
220	Carbon doping in metalorganic vapor phase epitaxy. *Journal of Crystal Growth*, **1994**, 145, 382-389	1.6	52
219	Diameter-dependent composition of vapor-liquid-solid grown Si(1-x)Ge(x) nanowires. *Nano Letters*, **2007**, 7, 3241-5	11.5	51
218	Wafer-Scale Epitaxial Growth of Unidirectional WS Monolayers on Sapphire. *ACS Nano*, **2021**, 15, 2532-2541	14.7	51
217	Tin-Catalyzed Plasma-Assisted Growth of Silicon Nanowires. *Journal of Physical Chemistry C*, **2011**, 115, 3833-3839	3.8	50
216	Effect of damage by 2MeV He ions on the normal and superconducting properties of magnesium diboride. *Applied Physics Letters*, **2005**, 86, 012508	3.4	49
215	Controlled synthesis of 2D transition metal dichalcogenides: from vertical to planar MoS 2. *2D Materials*, **2017**, 4, 025029	5.9	48
214	Correlation of growth stress and structural evolution during metalorganic chemical vapor deposition of GaN on (111) Si. *Applied Physics Letters*, **2006**, 88, 041904	3.4	46
213	Effect of AlN interlayers on growth stress in GaN layers deposited on (111) Si. *Applied Physics Letters*, **2005**, 87, 142101	3.4	44
212	Internal photoemission measurement of Schottky barrier height for Ni on AlGaN/GaN heterostructure. *Applied Physics Letters*, **1998**, 73, 3917-3919	3.4	44
211	Enhancement of flux pinning and high-field critical current density in carbon-alloyed MgB2 thin films. *Physical Review B*, **2006**, 74,	3.3	42
210	Considerations for Utilizing Sodium Chloride in Epitaxial Molybdenum Disulfide. *ACS Applied Materials & Interfaces*, **2018**, 10, 40831-40837	9.5	42
209	The nature of catalyst particles and growth mechanisms of GaN nanowires grown by Ni-assisted metal-organic chemical vapor deposition. *Nanotechnology*, **2009**, 20, 085610	3.4	41
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207	Tensile stress generation and dislocation reduction in Si-doped AlxGa1−xN films. *Journal of Applied Physics*, **2009**, 106, 023506	2.5	37
206	Steady-state tensile stresses during the growth of polycrystalline films. *Acta Materialia*, **2007**, 55, 4973-4982	8.3	37
205	Effect of disorder in MgB2 thin films. *Physical Review B*, **2005**, 71,	3.3	37
204	Structural and electrical properties of epitaxial Bi2Se3 thin films grown by hybrid physical-chemical vapor deposition. *Applied Physics Letters*, **2012**, 100, 162110	3.4	36
203	Nickel and nickel silicide Schottky barrier contacts to n-type silicon nanowires. *Journal of Vacuum Science & Technology B*, **2008**, 26, 1592		36
202	In situ stress measurements during the MOCVD growth of AlN buffer layers on (1 1 1) Si substrates. *Journal of Crystal Growth*, **2004**, 261, 294-300	1.6	36
201	Influence of Carbon in Metalorganic Chemical Vapor Deposition of Few-Layer WSe2 Thin Films. *Journal of Electronic Materials*, **2016**, 45, 6273-6279	1.9	35
200	Effect of damage by 2 MeV He ions and annealing on Hc2 in MgB2 thin films. *Applied Physics Letters*, **2005**, 87, 072507	3.4	35
199	Room-Temperature Active Modulation of Valley Dynamics in a Monolayer Semiconductor through Chiral Purcell Effects. *Advanced Materials*, **2019**, 31, e1904132	24	34
198	In situ axially doped n-channel silicon nanowire field-effect transistors. *Nano Letters*, **2008**, 8, 4359-64	11.5	34
197	Modification of critical current density of MgB2 films irradiated with 200 MeV Ag ions. *Applied Physics Letters*, **2004**, 84, 2352-2354	3.4	34
196	Fabrication and characterisation of enhanced barrier AlGaN/GaN HFET. *Electronics Letters*, **1999**, 35, 602	1.1	34
195	Temperature-Dependent Properties of Nearly Ideal ZnO Schottky Diodes. *IEEE Transactions on Electron Devices*, **2009**, 56, 2160-2164	2.9	33
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193	Dependence of penetration depth, microwave surface resistance and energy gap of MgB2 thin films on their normal-state resistivity. *Superconductor Science and Technology*, **2005**, 18, L1-L4	3.1	33
192	Schottky Diodes on MOCVD Grown AlGaN Films. *MRS Internet Journal of Nitride Semiconductor Research*, **1998**, 3, 1		33
191	Growth and Characterization of Unintentionally Doped GaSb Nanowires. *Journal of Electronic Materials*, **2010**, 39, 355-364	1.9	31
190	SQUID magnetometer operating at 37 K based on nanobridges in epitaxial MgB2 thin films. *Applied Physics Letters*, **2005**, 87, 192505	3.4	31

189	Effect of indium surfactant on stress relaxation by V-defect formation in GaN epilayers grown by metalorganic chemical vapor deposition. *Journal of Applied Physics*, **2010**, 108, 093511	2.5	30
188	Facet roughness analysis for InGaN/GaN lasers with cleaved facets. *Applied Physics Letters*, **1998**, 73, 1925-1927	3.4	30
187	Progress in the deposition of MgB2thin films. *Superconductor Science and Technology*, **2004**, 17, S196-S201	3.1	30
186	Stochastic resonance in MoS photodetector. *Nature Communications*, **2020**, 11, 4406	17.4	30
185	Planar MgB2 superconductor-normal metal-superconductor Josephson junctions fabricated using epitaxial MgB2/TiB2 bilayers. *Applied Physics Letters*, **2006**, 88, 222511	3.4	29
184	Chalcogen Precursor Effect on Cold-Wall Gas-Source Chemical Vapor Deposition Growth of WS2. *Crystal Growth and Design*, **2018**, 18, 4357-4364	3.5	28
183	Microwave noise performance of AlGaN/GaN HEMTs. *Electronics Letters*, **2000**, 36, 175	1.1	28
182	Epitaxial Growth of Two-Dimensional Layered Transition Metal Dichalcogenides. *Annual Review of Materials Research*, **2020**, 50, 155-177	12.8	27
181	Metalorganic chemical vapor deposition of N-polar GaN films on vicinal SiC substrates using indium surfactants. *Applied Physics Letters*, **2012**, 100, 021913	3.4	27
180	Dislocation bending and tensile stress generation in GaN and AlGaN films. *Journal of Crystal Growth* , **2012**, 359, 35-42	1.6	27
179	Formation of nickel germanide contacts to Ge nanowires. *Applied Physics Letters*, **2010**, 97, 263116	3.4	27
178	Oxidation of silicon nanowires for top-gated field effect transistors. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2008**, 26, 370-374	2.9	27
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176	A near-field scanning optical microscopy study of the photoluminescence from GaN films. *Applied Physics Letters*, **1996**, 69, 3519-3521	3.4	27
175	Suppression of the vapor-liquid-solid growth of silicon nanowires by antimony addition. *Nanotechnology*, **2009**, 20, 025607	3.4	26
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173	Multi-scale modeling of gas-phase reactions in metal-organic chemical vapor deposition growth of WSe2. *Journal of Crystal Growth*, **2019**, 527, 125247	1.6	25
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171	Evolution of threading dislocations in MOCVD-grown GaN films on (111) Si substrates. *Journal of Crystal Growth*, **2007**, 300, 217-222	1.6	25
170	Vibrational and optical properties of GaN nanowires synthesized by Ni-assisted catalytic growth. *Nanotechnology*, **2007**, 18, 445704	3.4	25
169	Scalable BEOL compatible 2D tungsten diselenide. *2D Materials*, **2020**, 7, 015029	5.9	25
168	Fundamental limitations in transferred CVD graphene caused by Cu catalyst surface morphology. *Carbon*, **2020**, 163, 95-104	10.4	24
167	Growth of thick p-type SiC epitaxial layers by halide chemical vapor deposition. *Journal of Crystal Growth*, **2008**, 310, 4088-4093	1.6	24
166	Substrate effects on GaN photoconductive detector performance. *Applied Physics Letters*, **1999**, 75, 25-27	3.4	24
165	Scanning electron microscope studies of AlGaN films grown by organometallic vapor phase epitaxy. *Solid-State Electronics*, **1998**, 42, 637-646	1.7	23
164	. *IEEE Transactions on Applied Superconductivity*, **2005**, 15, 3234-3237	1.8	23
163	In situ growth of MgB/sub 2/ thin films by hybrid physical-chemical vapor deposition. *IEEE Transactions on Applied Superconductivity*, **2003**, 13, 3233-3237	1.8	23
162	Electron scattering dependence of dendritic magnetic instability in superconducting MgB2 films. *Applied Physics Letters*, **2004**, 85, 5284-5286	3.4	23
161	Effect of AlN buffer layers on the surface morphology and structural properties of N-polar GaN films grown on vicinal C-face SiC substrates. *Journal of Crystal Growth*, **2013**, 377, 51-58	1.6	22
160	High-Jc MgB2 Josephson junctions with operating temperature up to 40 K. *Applied Physics Letters*, **2010**, 96, 042506	3.4	22
159	Raman Scattering from Si1-xGex Alloy Nanowires. *Journal of Physical Chemistry C*, **2008**, 112, 3209-3215	3.8	22
158	In situ observation of coalescence-related tensile stresses during metalorganic chemical vapor deposition of GaN on sapphire. *Applied Physics Letters*, **2005**, 86, 261907	3.4	22
157	Multidimensional thermal analysis of an ultrawide bandgap AlGaN channel high electron mobility transistor. *Applied Physics Letters*, **2019**, 115, 153503	3.4	21
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153	In situ measurement of stress generation arising from dislocation inclination in AlxGa1−xN:Si thin films. *Applied Physics Letters*, **2008**, 93, 111910	3.4	19
152	Characterisation of rhenium Schottky contacts on n-type AlxGa1−xN. *Electronics Letters*, **1999**, 35, 745	1.1	19
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150	Thin Film Transistors Using Wafer-Scale Low-Temperature MOCVD WSe2. *Journal of Electronic Materials*, **2016**, 45, 6280-6284	1.9	18
149	Understanding Interlayer Coupling in TMD-hBN Heterostructure by Raman Spectroscopy. *IEEE Transactions on Electron Devices*, **2018**, 65, 4059-4067	2.9	18
148	Ultrafast Electrical Measurements of Isolated Silicon Nanowires and Nanocrystals. *Journal of Physical Chemistry Letters*, **2014**, 5, 2050-7	6.4	18
147	Modeling studies of the chemical vapor deposition of boron films from B2H6. *Journal of Crystal Growth*, **2007**, 299, 358-364	1.6	18
146	Nanoscale disorder in high critical field, carbon-doped MgB2 hybrid physical-chemical vapor deposition thin films. *Applied Physics Letters*, **2007**, 91, 082513	3.4	18
145	Degradation of MgB/sub 2/ thin films in water. *IEEE Transactions on Applied Superconductivity*, **2005**, 15, 224-227	1.8	18
144	Current limitation after pinch-off in AlGaN/GaN FETs. *MRS Internet Journal of Nitride Semiconductor Research*, **2000**, 5, 1		18
143	Photoelastic waveguides and the controlled introduction of strain in III-V semiconductors by means of thin film technology. *Journal of Applied Physics*, **1995**, 78, 236-244	2.5	18
142	Effect of substrate on the growth and properties of thin 3R NbS2 films grown by chemical vapor deposition. *Journal of Crystal Growth*, **2018**, 486, 137-141	1.6	17
141	High-field properties of carbon-doped MgB2thin films by hybrid physical□hemical vapor deposition using different carbon sources. *Superconductor Science and Technology*, **2011**, 24, 125014	3.1	17
140	Effect of reactor pressure on catalyst composition and growth of GaSb nanowires. *Journal of Crystal Growth*, **2010**, 312, 514-519	1.6	17
139	Fabrication of Cobalt Silicide Nanowire Contacts to Silicon Nanowires. *Journal of the Electrochemical Society*, **2003**, 150, G577	3.9	17
138	Terahertz surface impedance of epitaxial MgB2 thin film. *Applied Physics Letters*, **2005**, 87, 092503	3.4	17
137	Atomic layer deposition of ZnO on MoS2 and WSe2. *Applied Surface Science*, **2019**, 480, 43-51	6.7	16
136	Single wire radial junction photovoltaic devices fabricated using aluminum catalyzed silicon nanowires. *Nanotechnology*, **2011**, 22, 445401	3.4	16

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133	Growth of Thick MgB2 Films by Impinging-Jet Hybrid Physical-Chemical Vapor Deposition. *Advanced Materials*, **2008**, 20, 319-323	24	16
132	The effect of polarity on MOCVD growth of thick InGaN. *Applied Physics Letters*, **2017**, 110, 022101	3.4	15
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130	Evolution of surface morphology and film stress during MOCVD growth of InN on sapphire substrates. *Journal of Crystal Growth*, **2004**, 269, 128-133	1.6	15
129	Raman scattering in pure and carbon-doped MgB2 films. *Physical Review B*, **2005**, 71,	3.3	15
128	Growth studies of erbium-doped GaAs deposited by metalorganic vapor phase epitaxy using novel cyclopentadienyl-based erbium sources. *Journal of Applied Physics*, **1994**, 76, 1585-1591	2.5	15
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122	Defect creation in WSe with a microsecond photoluminescence lifetime by focused ion beam irradiation. *Nanoscale*, **2020**, 12, 2047-2056	7.7	13
121	Influence of growth stress on the surface morphology of N-polar GaN films grown on vicinal C-face SiC substrates. *Applied Physics Letters*, **2013**, 103, 241908	3.4	12
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118	Gas phase equilibrium limitations on the vapor□quid□olid growth of epitaxial silicon nanowires using SiCl4. *Journal of Materials Research*, **2011**, 26, 2207-2214	2.5	12

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116	SF6/O2 plasma effects on silicon nitride passivation of AlGaN/GaN high electron mobility transistors. *Applied Physics Letters*, **2006**, 89, 223523	3.4	12
115	AlGaN/GaN MODFETs on semi-insulating SiC with 3 W/mm at 20 GHz. *Electronics Letters*, **2000**, 36, 1234	1.1	12
114	A simple reflectance method for estimation of the Al mole fraction of bulk AlGaN and AlGaN/GaN heterostructures. *Applied Physics Letters*, **1999**, 75, 1419-1421	3.4	12
113	Effect of Ge doping on growth stress and conductivity in AlxGa1-xN. *Applied Physics Letters*, **2019**, 114, 142101	3.4	11
112	Scalable Substitutional Re-Doping and its Impact on the Optical and Electronic Properties of Tungsten Diselenide. *Advanced Materials*, **2020**, 32, e2005159	24	11
111	Interdependence of Electronic and Thermal Transport in AlxGa1-xN Channel HEMTs. *IEEE Electron Device Letters*, **2020**, 41, 461-464	4.4	11
110	Gate recessing of GaN MESFETs using photoelectrochemical wet etching. *Electronics Letters*, **1999**, 35, 2140	1.1	11
109	Light-matter coupling in large-area van der Waals superlattices. *Nature Nanotechnology*, **2021**,	28.7	11
108	Monolayer MoS2 on sapphire: an azimuthal reflection high-energy electron diffraction perspective. *2D Materials*, **2021**, 8, 025003	5.9	11
107	Hexagonal Boron Nitride Crystal Growth from Iron, a Single Component Flux. *ACS Nano*, **2021**, 15, 7032-7039	16.7	11
106	Aluminum-catalyzed silicon nanowires: Growth methods, properties, and applications. *Applied Physics Reviews*, **2016**, 3, 040806	17.3	11
105	Modeling for Structural Engineering and Synthesis of Two-Dimensional WSe2 Using a Newly Developed ReaxFF Reactive Force Field. *Journal of Physical Chemistry C*, **2020**, 124, 28285-28297	3.8	10
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103	Multi-wafer batch synthesis of graphene on Cu films by quasi-static flow chemical vapor deposition. *2D Materials*, **2019**, 6, 045032	5.9	10
102	Molecular Doping Control at a Topological Insulator Surface: F4-TCNQ on Bi2Se3. *Journal of Physical Chemistry C*, **2014**, 118, 14860-14865	3.8	10
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